

ABSTRACT

The present invention provides an Ag-In alloy sputtering target which can reduce the occurrence of abnormal electrical discharge or splashing in sputtering to form a reflection electrode film formed from Ag-In alloy. The Ag-In alloy sputtering target
5 of the present invention contains 0.1 at% to 1.5 at% of In and the balance including Ag and inevitable impurities. The amount of each of elements Si, Cr, Fe and Ni are equal to or less than 30ppm and the sum of their amounts is equal to or less than 90ppm.